

### isc Silicon PNP Darlington Power Transistor

### 2SB1470

#### **DESCRIPTION**

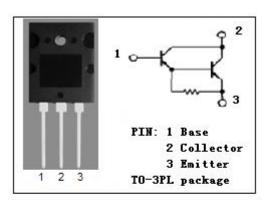
- · High forward current transfer ratio hFE
- Low collector to emitter saturation voltage VCE(sat)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

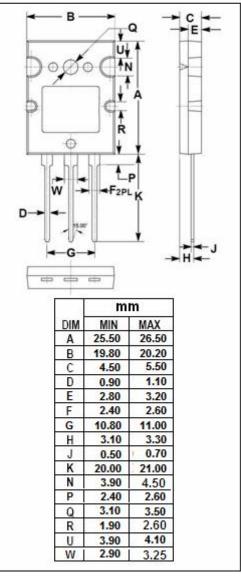
### **APPLICATIONS**

- Designed for power amplification
- · Optimum for 120W HiFi output applications.

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-160	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-160	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V	
lc	Collector Current-Continuous -8		А	
Ісм	Collector Current-Peak -15 A		А	
Pc	Collector Power Dissipation @ T <sub>C</sub> =25℃	150	W	
	Collector Power Dissipation @ T <sub>a</sub> =25 °C	3.5		
TJ	Junction Temperature 150 °C		$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	re Range -55~150 °C		







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### **ELECTRICAL CHARACTERISTICS**

### T<sub>C</sub>=25℃ unless otherwise specified

10-25 Curiless officials specified						
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -30mA; I <sub>B</sub> = 0	-160			٧
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	Ic= -7A; I <sub>B</sub> = -7mA			-3.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -7A; I <sub>B</sub> = -7mA			-3.0	٧
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -160V; I <sub>E</sub> = 0			-100	μА
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = -160V; I <sub>B</sub> = 0			-100	μ <b>А</b>
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-100	μ <b>А</b>
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V	1000			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -7A; V <sub>CE</sub> = -5V	3500		20000	
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -10V		20		MHz
Switching Times						
ton	Turn-on Time			1.0		μS
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = -7A; I <sub>B1</sub> = -I <sub>B2</sub> = -7mA,   V <sub>CC</sub> = -50V		1.5		μS
t <sub>f</sub>	Fall Time			1.2		μS

### ♦ h<sub>FE-2</sub> Classifications

Q	Р		
3500-10000	7000-20000		



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3

